

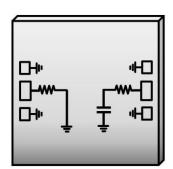
# GaAs IPD MMIC 50Ω Termination

### **Typical Applications**

- Communication Systems
- Point to Point Radio
- Fiber Optics
- Test Equipment
- Wideband Military & Space

#### **Features**

- Broadband 50-Ohm Termination
- AC and DC coupled RF Port Options
- Return Loss: 19.7dB @ 25GHz
- Die Size: 1.00 x 0.75 x 0.1 mm; Matches AGATNxx, AGLPFxxx, AGBPFxxx, and AGBSFxxx series MMICs



### **Electrical Specifications (TA = +25°C)**

Parameter	Units	Minimum	Typical	Maximum
Frequency (DC Coupled)	GHz	DC		50.0
(AC Coupled)	GHZ	0.25		50.0
Return Loss	dB	12	18	23
Package Type			Die	

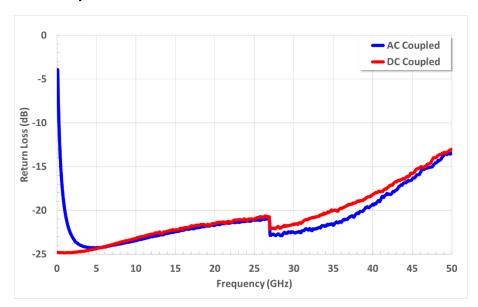




GaAs IPD MMIC  $50\Omega$  Termination

## **Performance Graphs**

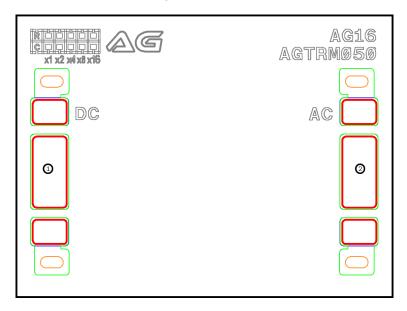
## **Return Loss (Simulated)**





GaAs IPD MMIC 50Ω Termination

## **Outline Drawing (DXF outline available)**



## **Pad Descriptions**

Pad	Function	Pad Size	Description
1	RFIN_DC	101x200μm	DC coupled 50Ω Matched
2	RFIN_AC	101x200μm	AC coupled 50Ω Matched
Die Bottom	GND	Backside	Epoxy/Solder to Baseplate

## **Absolute Maximum Ratings**

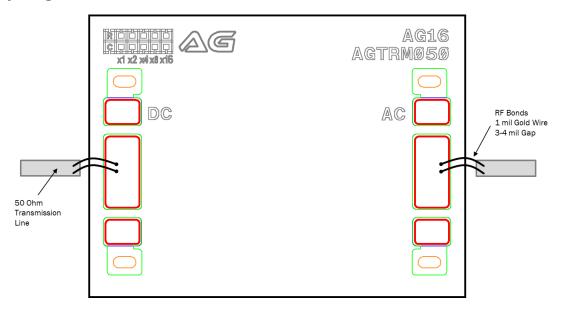
Parameter	Rating
Drain Bias Voltage (VDD)	No Bias
RF Input Power (RFIN)	+20dBm*
Channel Temperature	150°C
Storage Temperature	-65 to 150°C
Operating Temperature	-55 to 85°C

<sup>\*</sup>To be tested



# GaAs IPD MMIC 50Ω Termination

## **Assembly Diagrams**



### **Assembly Notes:**

- 1. Die Thickness is 100μm
- 2. Bondpad metallization: 7µm gold
- 3. Backside metallization: 4.5µm gold
- 4. Silver Epoxy or AuSn Eutectic attach MMIC



GP-4 (Gel-Pak)

